

30V N-Channel Enhancement Mode MOSFET

DESCRIPTION

The STN3400A is the N-Channel logic enhancement mode power field effect transistor is produced using high cell density, advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation gate as 2.5V. This device is suitable for use as a load switch or other general applications.

STN3400AS-TRG ROHS Compliant This is Halogen Free

FEATURE

- ◆ 30V/5.6A, $R_{DS(ON)} = 28m\Omega (typ.) @ V_{GS} = 10V$
- ◆ 30V/5.0A, $R_{DS(ON)} = 30m\Omega (typ.) @ V_{GS} = 4.5V$
- ◆ 30V/3.2A, $R_{DS(ON)} = 35m\Omega (typ.) @ V_{GS} = 2.5V$
- ◆ Super high density cell design for extremely low $R_{DS(ON)}$
- ◆ Exceptional on-resistance and Maximum DC current capability

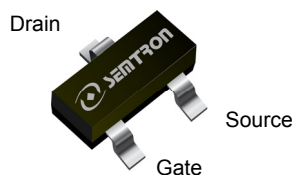
APPLICATIONS

- ◆ Power Management in Note book
- ◆ Portable Equipment
- ◆ DSC
- ◆ LCD Display inverter
- ◆ Battery Powered System
- ◆ DC/DC Converter

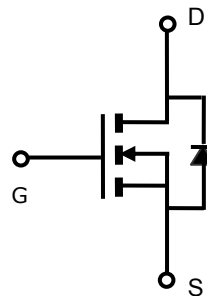


N-Channel Enhancement Mode MOSFET

PIN CONFIGURATION



SOT-23
Top View



PART NUMBER INFORMATION

$\frac{\text{ST N } 3400\text{A S - TR G}}{\text{a b c d e f}}$	<p>a : Company name. b : Channel type. c : Product Serial number. d : Package code e : Handling code f : Green product code</p>
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ORDERING INFORMATION

Part Number	Package Code	Handling Code	Shipping
STN3400AS-TRG	S : SOT-23	TR : Tape&Reel	3K/Reel

- ※ Year Code : 0 ~ 9, 2010 : 0
- ※ Week Code : A(1~2) ~ Z(53~54)
- ※ SOT-23L : Only available in tape and reel packaging.

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ Unless otherwise noted)

Symbol	Parameter	Typical	Unit	
V_{DSS}	Drain-Source Voltage	30	V	
V_{GSS}	Gate-Source Voltage	± 12	V	
I_D	Continuous Drain Current ($T_C=25^\circ\text{C}$) ^A	5.6	A	
	Continuous Drain Current ($T_C=70^\circ\text{C}$) ^A			
I_{DM}	Pulsed Drain Current ^B	20	A	
P_D	Power Dissipation	$T_A=25^\circ\text{C}$	1.0	W
		$T_A=70^\circ\text{C}$	0.7	
T_J	Operation Junction Temperature	-55 to 150	$^\circ\text{C}$	
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$	

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged.
 Absolute maximum ratings are stress ratings only and functional device operation is not implied.

THERMAL DATA

Symbol	Parameter	Typ	Max	Unit	
$R_{\theta JA}$	Thermal Resistance-Junction to Ambient ^A	Steady-State	-	120	$^\circ\text{C}/\text{W}$
$R_{\theta JL}$	Thermal Resistance Junction to Lead ^A	Steady-State	-	85	$^\circ\text{C}/\text{W}$

ELECTRICAL CHARACTERISTICS (T_J = 25°C Unless otherwise noted)

Symbol	Parameter	Condition	Min	Typ	Max	Unit
Static Parameters						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	30			V
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	0.6		1.2	V
I _{GSS}	Gate Leakage Current	V _{DS} =0V, V _{GS} =±12V			±100	nA
I _{DSS}	Zero Gate Voltage, Drain-Source Leakage Current	V _{DS} =24V, V _{GS} =0V T _J =25°C			1	μA
		V _{DS} =24V, V _{GS} =0V T _J =55°C			5	
R _{DS(ON)}	Drain-source On-Resistance ^B	V _{GS} =10V, I _D =5.6A		28	33	mΩ
		V _{GS} =4.5V, I _D =5.0A		30	35	
		V _{GS} =2.5V, I _D =3.2A		35	40	
G _{fs}	Forward Transconductance	V _{DS} =15V, I _D =5.0A		12		S
R _g	Gate Resistance	V _{GS} =0V, V _{DS} =0V, f=1MHz		1.5	3	Ω
Source-Drain Diode						
V _{SD}	Diode Forward Voltage	I _S =1.0A, V _{GS} =0V		0.7	1.0	V
I _S	Continuous Source Current ^{AD}				5.8	A
Dynamic Parameters						
Q _g (4.5V)	Total Gate Charge	V _{DS} =20V V _{GS} =4.5V I _D =5.8A		8.65		nC
Q _{gs}	Gate-Source Charge			1.26		
Q _{gd}	Gate-Drain Charge			1.85		
C _{iss}	Input Capacitance	V _{DS} =15V V _{GS} =0V f=1MHz		468		pF
C _{oss}	Output Capacitance			52.5		
C _{rss}	Reverse Transfer Capacitance			43.2		
t _{d(on)}	Turn-On Time	V _{DD} =15V I _D =4A		3.3	6.5	nS
t _r				42	77	
t _{d(off)}	Turn-Off Time	V _{GEN} =10V R _G =3.3Ω		22	43	
t _f				6.5	13	

Note:

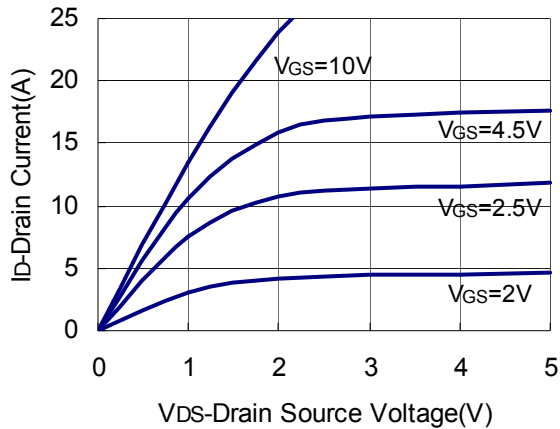
- The value of R_{θJA} is measured with the device mounted on 1in 2 FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C.
- The data tested by pulsed, pulse width ≤ 300μs, duty cycle ≤ 2%
- The EAS data shows Max. rating. The test condition is V_{DD}=25V, V_{GS}=10V, L=0.1mH.
- The data is theoretically the same as I_D and I_{DM}, in real applications, should be limited by total power dissipation.

The products and product specifications contained herein are subject to change without notice to improve performance characteristics. Consult us, or our representatives before use, to confirm that the information in this datasheet is up to date

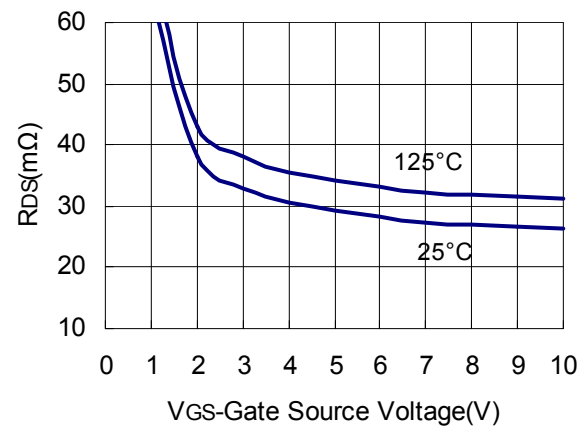
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TYPICAL CHARACTERISTICS (25°C Unless Note)

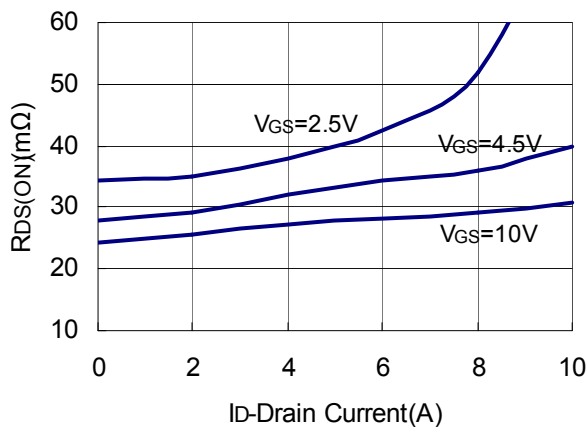
Output Characteristics



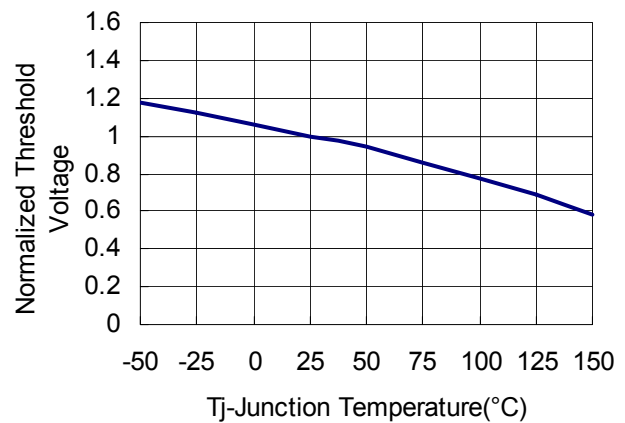
Drain-Source On Resistance



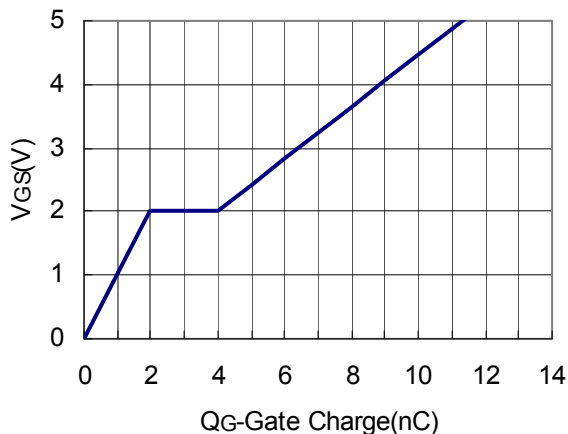
Drain Source On Resistance



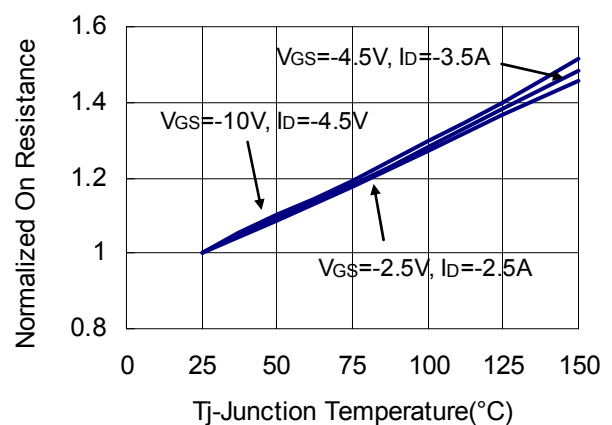
Gate Threshold Voltage



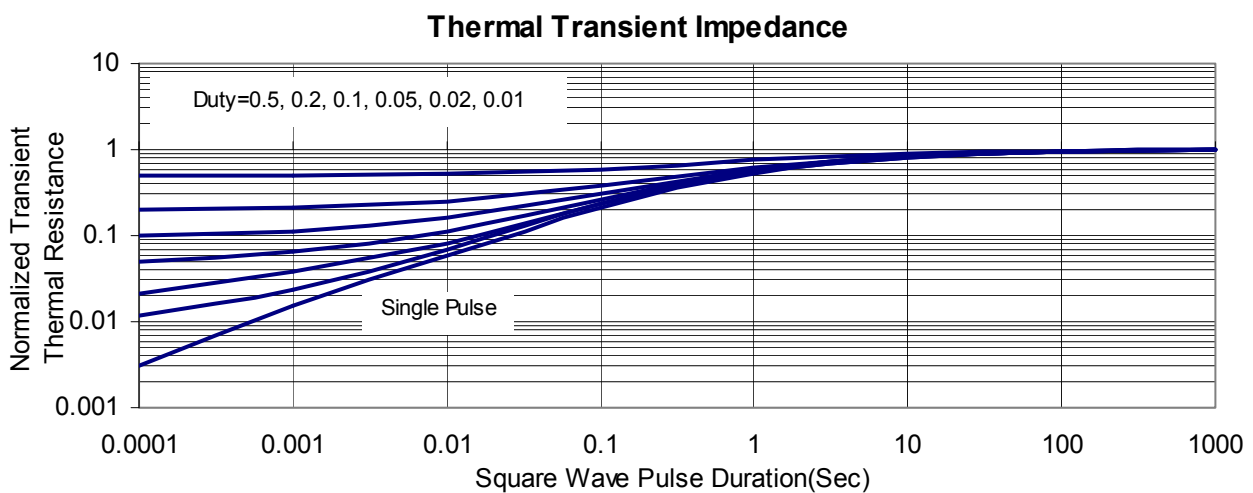
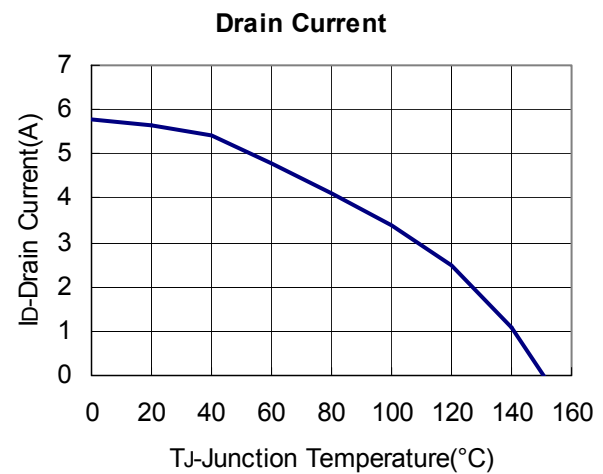
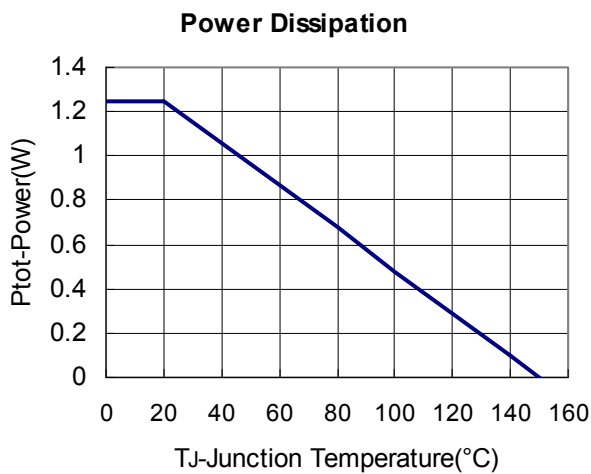
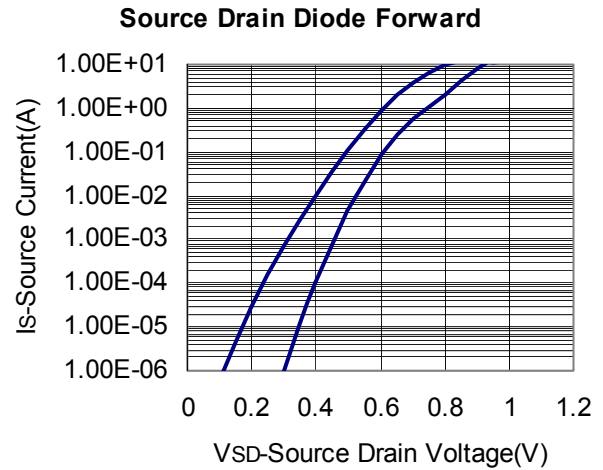
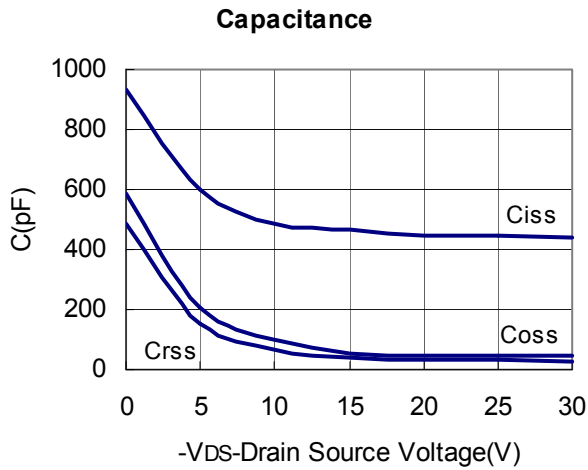
Gate Charge



Drain Source Resistance



TYPICAL CHARACTERISTICS (25°C Unless Note)



SOT-23 PACKAGE DIMENSIONS

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP.		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L1	0.550 REF.		0.022 REF.	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

